FEATURE

1). Isolated mounting base 2500V~

2). Pressure contact technology with Increased power cycling capability

3). Space and weight saving

TYPICAL APPLICATION

1). Various rectifiers

2). DC supply for PWM inverter

TYPE & Outline	V_{DSM},V_{RSM}	V_{DRM},V_{RRM}
MDA55-08-101F	900V	800V
MDA55-10-101F	1100V	1000V
MDA55-12-101F	1300V	1200V
MDA55-14-101F	1500V	1400V
MDA55-16-101F	1700V	1600V
MDA55-18-101F	1900V	1800V
MDA55-20-101F	2100V	2000V

Voltage Ratings

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled,T_c =100°C	150			55	A
$I_{F(RMS)}$	RMS forward current		150			86	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			8	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			1.30	KA
I^2t	I^2T for fusing coordination					8.45	A^2S*10^3
V_{FO}	Threshold voltage		150			0.80	V
r_F	Forward slop resistance					3.47	mΩ
V_{FM}	Peak forward voltage	I_{FM}=300A	25			1.45	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180°sine'Single side cooled per chip				0.70	°C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	At 180°sine'Single side cooled per chip				0.2	°C/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(max)		2500			V
F_m	Terminal connection torque(M5)				4		N·m
	Mounting torque(M6)				6		N·m
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight	110					g
Outline	101F						

PERFORMANCE CURVES FIGURE

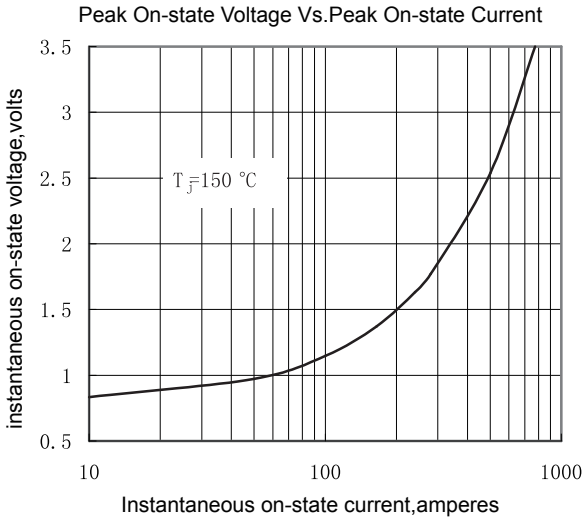


Fig.1

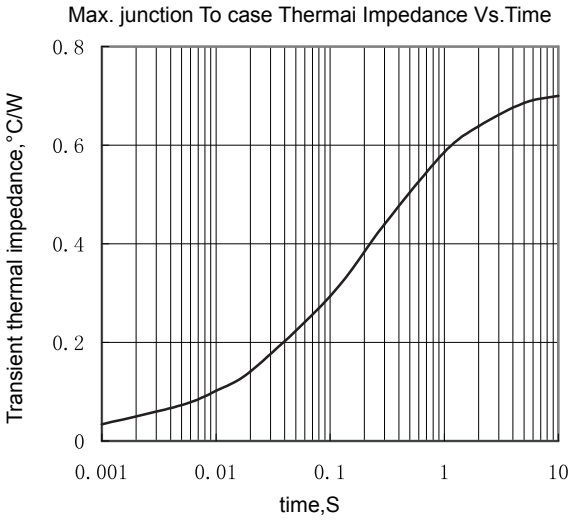


Fig.2

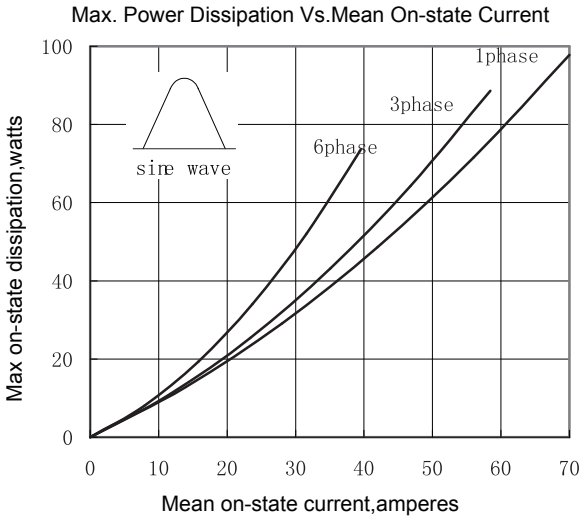


Fig.3

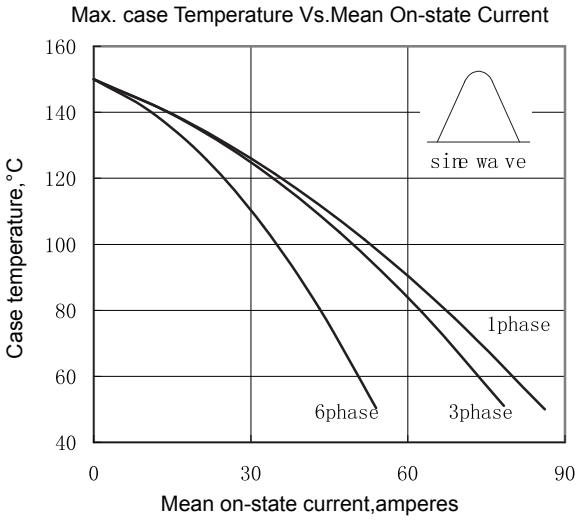


Fig.4

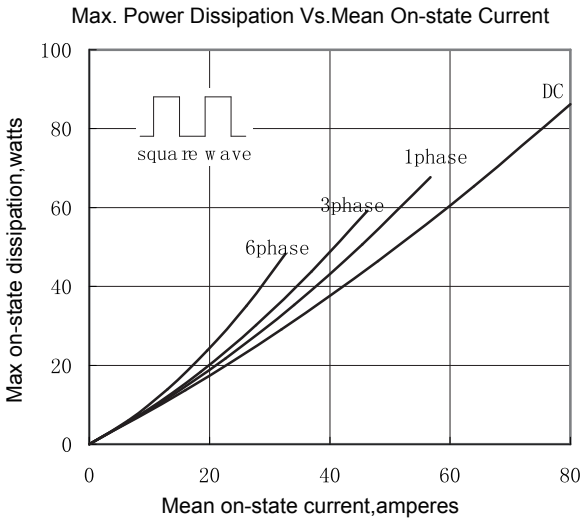


Fig.5

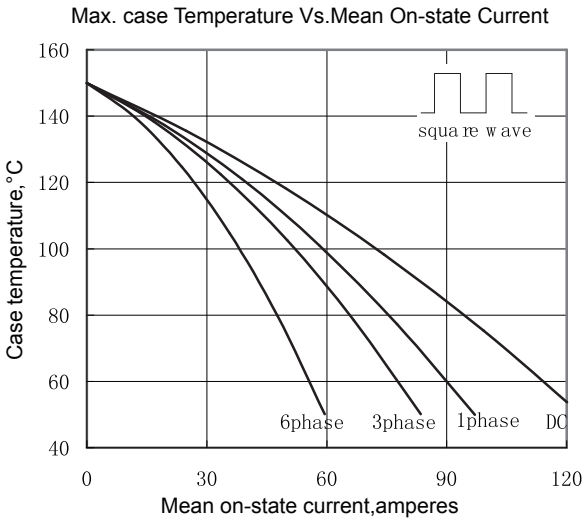


Fig.6

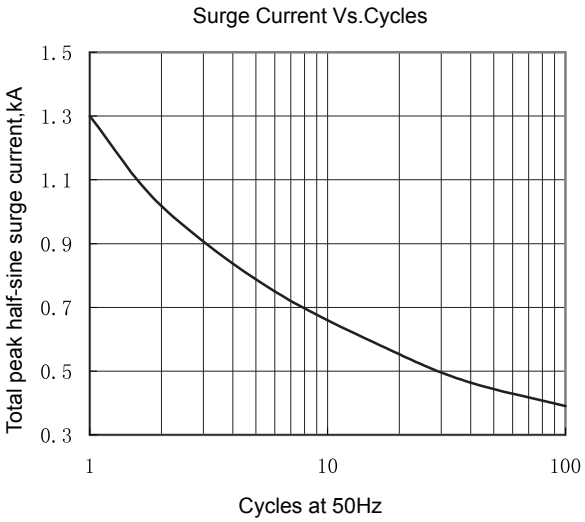


Fig.7

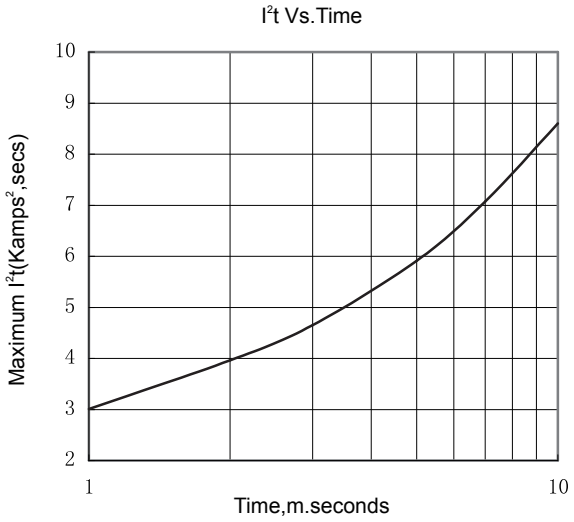
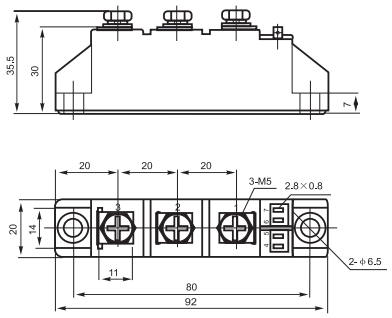


Fig.8

OUTLINE



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